REMARKS

The objection to claims 17-27 has been cured by correcting the spelling of germanate.

Reconsideration of the rejection of claim 1 is respectfully requested on the grounds that the cited reference does not teach selectively removing metal silicate. To be a selective removal, the item must be removed selectively relative to something else. For example, in Figure 2 of the present application, the layer 16a is removed without removing the material 18 or the material 14.

In contrast, in the prior Brask patent, the entire portion of the exposed, unmasked material is removed. In other words, there is no way that the structure shown in Figure 1D results except from a masking process. A masking process is non-selective. Everything that is exposed, except the mask, is removed. In contrast, in selective etching, the material that is selectively etched is selectively removed and everything else stays. It is the opposite of a masking process.

To substantiate the definition of "selectively," the attached Semiconductor Glossary is provided.

In view of these remarks, claim 1, its dependent claims, and claims 17 and 23 and their dependent claims should be in condition for allowance. Claim 7 and its dependent claims were already indicated to be allowable.

Respectfully submitted,

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Notes

Term (Index)	Definition
selective etching	etching processes in which one material is etched rapidly while the other is etched very slowly or not etched at all; Example - HF:water solution is etching SiO2 very rapidly while not etching silicon.
anisotropic etch	etch in which etch rate in the direction normal to the surface is much higher than in direction parallel to the surface; no undercutting i.e. lateral distortion of pattern is minimized; needed to define very tight geometries.

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